

CMDD2004
SUPERmini™
SURFACE MOUNT
HIGH VOLTAGE SWITCHING DIODE

SUPERmini™

SOD-323 CASE

Central™

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMDD2004 type is a high voltage silicon switching diode manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, designed for applications requiring high voltage capability. Marking code is **C24**.

MAXIMUM RATINGS: (T_A=25°C)

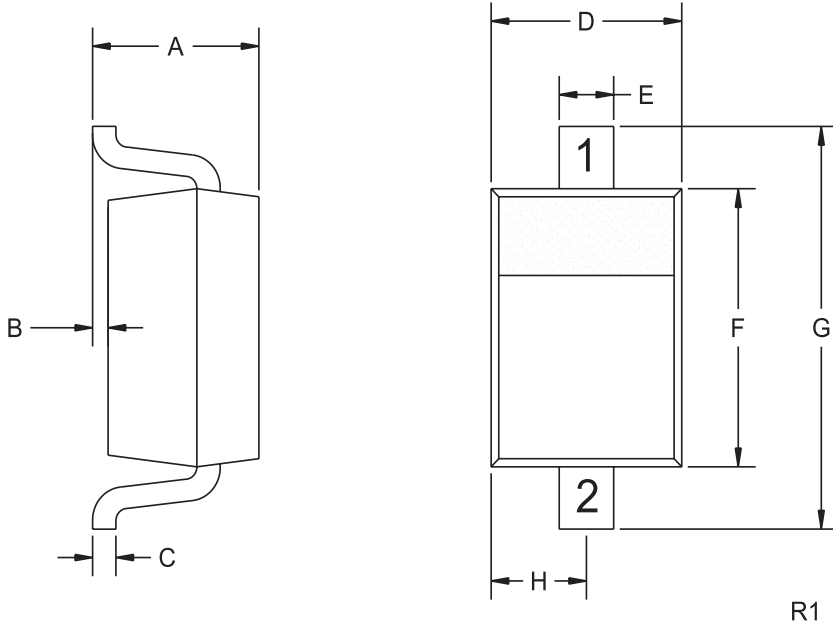
	SYMBOL		UNITS
Continuous Reverse Voltage	V _R	240	V
Peak Repetitive Reverse Voltage	V _{RRM}	300	V
Peak Repetitive Reverse Current	I _O	200	mA
Continuous Forward Current	I _F	225	mA
Peak Repetitive Forward Current	I _{FRM}	625	mA
Forward Surge Current, tp=1 μsec.	I _{FSM}	4000	mA
Forward Surge Current, tp=1 sec.	I _{FSM}	1000	mA
Power Dissipation	P _D	250	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	500	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
B _{VR}	I _R =100μA	300		V
I _R	V _R =240V		100	nA
I _R	V _R =240V, T _A =150°C		100	μA
V _F	I _F =100mA		1.0	V
C _T	V _R =0, f=1 MHz		5.0	pF
t _{rr}	I _F =I _R =30mA, Rec. To 3.0mA, R _L =100Ω		50	ns

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DIODE

SOD-323 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Cathode
- 2) Anode

MARKING CODE: C24

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.039	0.043	1.00	1.10
B	0.000	0.004	0.00	0.10
C	0.005	0.008	0.14	0.22
D	0.045	0.053	1.15	1.35
E	0.011	0.015	0.28	0.38
F	0.063	0.071	1.60	1.80
G	0.094	0.102	2.40	2.60
H	0.023	0.027	0.58	0.68

SOD-323 (REV: R1)

R1 (7-August 2001)